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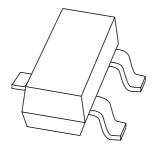
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Kind regards,

Team Nexperia

# DISCRETE SEMICONDUCTORS

# DATA SHEET



# **BCX71 series**PNP general purpose transistors

Product data sheet Supersedes data of 1999 Apr 20 2004 Feb 16



# PNP general purpose transistors

## **BCX71** series

#### **FEATURES**

• Low current (max. 100 mA)

• Low voltage (max. 45 V)

• Low noise.

#### **APPLICATIONS**

- Low level, low noise, low frequency applications in hybrid circuits
- · General purpose switching and amplification.

#### **DESCRIPTION**

PNP transistor in a plastic SOT23 package. NPN complements: BCX70 series.

#### **MARKING**

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
BCX71H	BH*
BCX71J	BJ*
BCX71K	BK*

#### Note

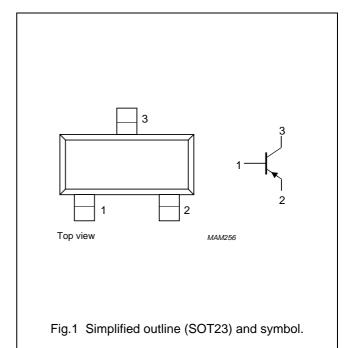
1. \* = p : Made in Hong Kong.

\* = t : Made in Malaysia.

\* = W : Made in China.

#### **PINNING**

PIN	DESCRIPTION
1	base
2	emitter
3	collector



#### **ORDERING INFORMATION**

TYPE	PACKAGE					
NUMBER	NAME	VERSION				
BCX71H	_	plastic surface mounted package; 3 leads	SOT23			
BCX71J						
BCX71K						

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# PNP general purpose transistors

BCX71 series

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	-45	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	-45	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	-5	V
I <sub>C</sub>	collector current (DC)		_	-100	mA
I <sub>CM</sub>	peak collector current		_	-200	mA
I <sub>BM</sub>	peak base current		_	-200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	_	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	500	K/W

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

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# PNP general purpose transistors

BCX71 series

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = -45 V	_	-	-20	nA
		I <sub>E</sub> = 0; V <sub>CB</sub> = -45 V; T <sub>amb</sub> = 150 °C	_	_	-20	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$I_C = 0; V_{EB} = -4 V$	_	_	-20	nA
h <sub>FE</sub>	DC current gain	$I_C = -10 \mu A; V_{CE} = -5 V$				
	BCX71H		30	_	_	
	BCX71J		40	_	_	
	BCX71K		100	_	_	
	DC current gain	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$				
	BCX71H		180	_	310	
	BCX71J		250	_	460	
	BCX71K		380	_	630	
	DC current gain	$I_C = -50 \text{ mA}$ ; $V_{CE} = -1 \text{ V}$ ; note 1				
	BCX71H		80	_	_	
	BCX71J		100	_	_	
	BCX71K		110	_	_	
V <sub>CEsat</sub>	collector-emitter saturation	$I_C = -10 \text{ mA}; I_B = -0.25 \text{ mA}$	-60	_	-250	mV
	voltage	$I_C = -50 \text{ mA}$ ; $I_B = -1.25 \text{ mA}$ ; note 1	-120	_	-550	mV
V <sub>BEsat</sub>	base-emitter saturation	$I_C = -10 \text{ mA}; I_B = -0.25 \text{ mA}$	-600	_	-850	mV
	voltage	$I_C = -50 \text{ mA}$ ; $I_B = -1.25 \text{ mA}$ ; note 1	-680	_	-1050	mV
$V_{BE}$	base-emitter voltage	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	-600	-650	-750	mV
		$I_C = -10 \mu A; V_{CE} = -5 V$	_	-550	_	mV
		$I_C = -50 \text{ mA}; V_{CE} = -1 \text{ V}; \text{ note 1}$	_	-720	_	mV
C <sub>c</sub>	collector capacitance	$I_E = I_e = 0$ ; $V_{CB} = -10 \text{ V}$ ; $f = 1 \text{ MHz}$	_	4.5	_	pF
C <sub>e</sub>	emitter capacitance	$I_C = I_c = 0$ ; $V_{EB} = -0.5 \text{ V}$ ; $f = 1 \text{ MHz}$	_	11	_	pF
f <sub>T</sub>	transition frequency	$I_C = -10 \text{ mA}$ ; $V_{CE} = -5 \text{ V}$ ; $f = 100 \text{ MHz}$	100	-	_	MHz
F	noise figure	$I_C = -200 \ \mu A; \ V_{CE} = -5 \ V; \ R_S = 2 \ k\Omega; \ f = 1 \ kHz; \ B = 200 \ Hz$	_	2	6	dB

#### Note

1. Pulse test:  $t_p \leq 300~\mu s;~\delta \leq 0.02.$ 

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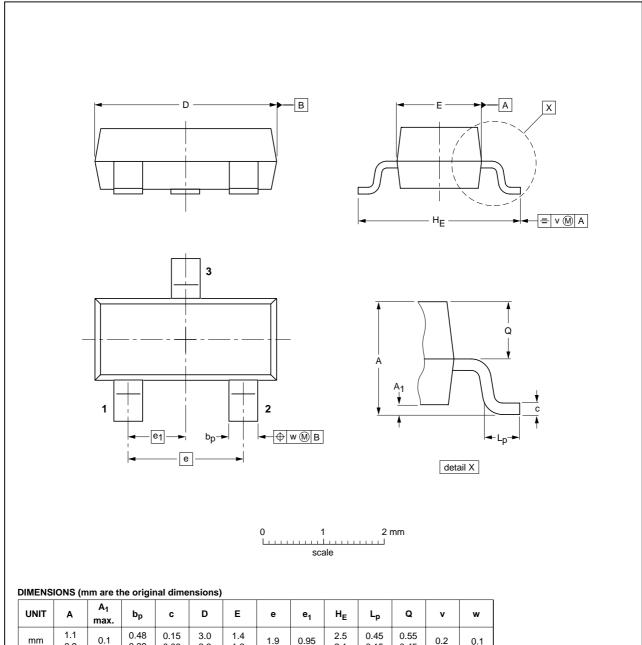
# PNP general purpose transistors

# BCX71 series

SOT23

#### **PACKAGE OUTLINE**

#### Plastic surface-mounted package; 3 leads



UNIT	Α	max.	bp	С	D	E	е	e <sub>1</sub>	HE	L <sub>p</sub>	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	C JEDEC JEITA PROJECTI		PROJECTION	ISSUE DATE	
SOT23		TO-236AB				<del>-04-11-04</del> 06-03-16

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## PNP general purpose transistors

BCX71 series

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

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